

IN THE CLAIMS

Please cancel claims 1-13 and add 14-17 as follows:

01 14. A method of manufacturing a semiconductor apparatus comprising the steps of:

5 forming a bypass film from an insulation film through which a leak current is able to easily flow as compared with a gate insulation film of a MIS transistor and forming a gate electrode which extends above said bypass film; and

performing a work process directed to the manufacture of the semiconductor apparatus while performing destaticization through said bypass film.

15. A method of manufacturing a semiconductor apparatus according to claim 14, further comprising the steps of:

selectively etching a gate insulation film of a region forming said bypass film to make the same thin after said gate insulation film of said MIS transistor has been formed; and

forming said gate electrode to have a pattern extending from a region of said MIS transistor to a portion above said bypass film.

20 16. A method of manufacturing a semiconductor apparatus according to claim 14, further comprising the steps of:

forming a first gate insulation film of said MIS, transistor, then selectively etching off said first gate insulation film at a region of said bypass film and forming a  
25 second gate insulation film which will become said bypass film; and

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then forming said gate electrode to have a pattern  
extending from a region of said MIS transistor to a portion  
above said bypass film.

17. A method of manufacturing a solid state image device  
5 comprising the steps of:

forming a bypass film through which a leak current is  
able to easily flow as compared with a gate insulation film,  
between a wiring for connecting each gate electrodes of a MOS  
transistor forming the pixel and a drain region, and

10 carrying out a work process while performing  
destaticization through said bypass film.

#### REMARKS

This amendment is filed to claim priority to the parent  
and Japanese priority application and to incorporate same by  
reference. Also, the subject matters of claims 9-11 and 13  
have been recast as claims 14-17, respectively.

Respectfully submitted,  
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